

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	14942	(poly\$1silicon or (poly\$1crystalline adj silicon)) same (oxide or SiO or "SiO.sub.2") same (selective or selectivity or selectively)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/18 09:01
L2	6254	(poly\$1silicon or (poly\$1crystalline adj silicon)) with (oxide or SiO or "SiO.sub.2") with (selective or selectivity or selectively)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/18 09:01
L3	4993	2 and gate	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/18 09:01
L4	4745	3 and @ay<="2003"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/18 09:03
L5	747	4 and (passivate or passiating or passivation)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/18 09:03
L6	306	4 and ((passivate or passiating or passivation) with (oxide or dioxide or SiO or "SiO.sub.2"))	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/18 09:03
L7	299	6 and (etch or etching)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/18 09:04
L8	201	7 and plasma	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/18 11:17
L9	70	8 and (silane or "SiF.sub.4" or "SiCl.sub.4" or "Si.sub.2 H.sub.6" or "SiHCl.sub.3" or "SiH.sub.2 Cl.sub.2")	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/18 09:04
L10	65	("5094712").URPN.	USPAT	OR	ON	2005/07/18 09:25
L11	21	8 and ((alumina or quartz) same (oxygen or oxide or "O.sub.2"))	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/18 12:55
L12	1	Puppo-Helene-Del.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/18 12:55
L13	25	Lin-Frank.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/18 12:55
L14	17	Lee-Chris.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/18 12:55

L15	1	Kamp-thomas-A.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/18 12:55
L16	12	Miller-Alan-J.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/18 12:55
L17	52	13 or 14 or 15 or 16	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/18 12:55
S1	1267	(poly\$1silicon or (poly\$1crystalline adj silicon)) same (etch or etching) same ("SiBr.sub.4" or "SiF.sub.2" or silane or "SiCl.sub. 4" or "SHCl.sub.3" or "SiH.sub.2 Cl.sub.2")	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/05/12 10:12
S2	1234	S1 and @ay<="2003"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/05/12 10:11
S3	740	((poly\$1silicon or (poly\$1crystalline adj silicon)) with (etch or etching)) same ("SiBr.sub. 4" or "SiF.sub.2" or silane or "SiCl. sub.4" or "SHCl.sub.3" or "SiH. sub.2 Cl.sub.2")	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/05/12 17:53
S4	723	S3 and @ay<="2003"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/05/12 10:14
S5	615	S4 and (doping or dopant or doped)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/05/12 10:14
S6	469	S5 and plasma	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/05/12 10:14
S7	426	S6 and gate	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/05/12 10:17
S8	347	S7 and (oxygen or "O.sub.2")	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/05/12 10:17
S9	314	S8 and (gate with (poly\$1silicon or (poly\$1crystalline adj silicon)))	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/05/12 10:19
S10	131	S3 and (passivating or passivation or passivated)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/05/12 17:53

S11	63	S10 not S8	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/05/12 17:54
S12	60	S11 and @ay<="2003"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/05/12 17:54
S13	1	"4490209".pn.	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/05/13 10:40
S14	72416	(poly\$1silicon or (poly\$1crystalline adj silicon)) same (oxide or SiO or "SiO.sub.2")	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/13 17:36
S15	52653	(poly\$1silicon or (poly\$1crystalline adj silicon)) same (oxide or SiO or "SiO.sub.2") same (gate or electrode)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/13 17:36
S16	38207	S15 and (etch or etching)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/13 17:37
S17	4861	S15 and ((etch or etching) same (silane or TEOS or "SiF.sub.4" or "SiCl.sub.4" or "Si.sub.2 H.sub.6" or "SiHCl.sub.3" or "SiH.sub.2 Cl. sub.2"))	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/13 17:40
S18	1860	S15 and ((etch or etching) with (silane or TEOS or "SiF.sub.4" or "SiCl.sub.4" or "Si.sub.2 H.sub.6" or "SiHCl.sub.3" or "SiH.sub.2 Cl. sub.2"))	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/13 18:05
S19	449	S18 and (passivate or passivating or passivation)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/13 18:07
S20	408	S19 and @ay<="2003"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/13 17:42
S21	381	S20 and ((gate or electrode) with (poly\$1silicon or poly\$1crystal\$4))	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/13 18:06
S22	381	S20 and ((gate or electrode) with (poly\$1silicon or (poly\$1crystal\$4 adj silicon)))	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/13 17:44
S23	336	S22 and (mask or masking or hard\$1mask or resist or photo\$1resist)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/13 18:06
S24	222	S23 and plasma	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/13 17:45

S25	457	S15 and ((etch or etching) with (silane or "SiF.sub.4" or "SiCl.sub.4" or "Si.sub.2 H.sub.6" or "SiHCl.sub.3" or "SiH.sub.2 Cl.sub.2"))	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/13 18:06
S26	438	S25 and @ay<="2003"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/13 18:06
S27	348	S26 and plasma	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/13 18:06
S28	312	S27 and ((gate or electrode) with (poly\$1silicon or poly\$1crystal\$4))	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/13 18:06
S29	296	S28 and (mask or masking or hard\$1mask or resist or photo\$1resist)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/13 18:06
S30	81	S29 and (passivate or passivating or passivation)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/13 18:20
S31	215	S29 not S30	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/13 18:20
S32	54192	(poly\$1silicon or (poly\$1crystalline adj silicon)) with (oxide or SiO or "SiO.sub.2")	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/18 09:00
S33	28411	S32 and (selective or selectivity or selectively)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/14 14:22
S34	10825	S32 same (selective or selectivity or selectively)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/14 14:22
S35	6254	S32 with (selective or selectivity or selectively)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/14 14:22
S36	12204	S33 and plasma	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/14 14:22
S37	2735	S35 and plasma	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/14 14:23
S38	725	S37 and (silane or "SiF.sub.4" or "SiCl.sub.4" or "Si.sub.2 H.sub.6" or "SiHCl.sub.3" or "SiH.sub.2 Cl.sub.2")	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/18 09:04
S39	387	S37 and ((silane or "SiF.sub.4" or "SiCl.sub.4" or "Si.sub.2 H.sub.6" or "SiHCl.sub.3" or "SiH.sub.2 Cl.sub.2") same (poly\$1silicon or poly\$1crystal\$3))	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/14 14:24

S40	387	S39 and (etch or etching)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/14 14:24
S41	381	S39 and @ay<="2003"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/14 14:24
S42	341	S41 and gate	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/14 14:25
S43	136	S42 and (passivate or passivating or passivation or polymer or polymeric)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/14 15:44
S44	1	"6653240".pn.	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/14 15:44
S45	9	("4411734" "4778563" "5007982" "5242536" "5310456" "5314576" "5354421" "5368686" "5436424").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/14 16:27
S46	4	("5705433").URPN.	USPAT	OR	ON	2005/07/14 17:04
S47	1	"5705433".pn.	USPAT	OR	ON	2005/07/14 17:05